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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	20MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	10
Program Memory Size	2KB (2K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 7x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-SSOP (0.173", 4.40mm Width)
Supplier Device Package	16-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10y46asp-50

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

O ROM, RAM capacities

Flash ROM	RAM	10 pins	16 pins
4 KB	512 B	-	R5F10Y47ASP Note 2
2 KB	256 B	R5F10Y16ASP	R5F10Y46ASP Note 2
1 KB	128 B	R5F10Y14ASP	R5F10Y44ASP Note 2

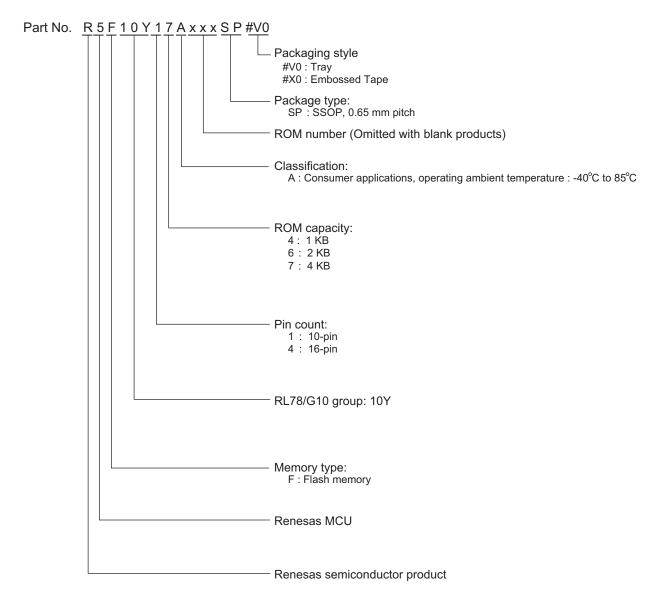
Notes 1. 16-pin products only

2. Under development

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

1.2 List of Part Number

Figure 1-1. Classification of Part Number



Pin count	Package	Part Number
10 pins	10-pin plastic LSSOP	R5F10Y16ASP#V0, R5F10Y16ASP#X0
	(4.4 × 3.6 mm, 0.65mmpitch)	R5F10Y14ASP#V0, R5F10Y14ASP#X0
16 pins	16-pin plastic SSOP	R5F10Y47ASP Note
	(4.4 × 5.0 mm, 0.65mmpitch)	R5F10Y46ASP Note
		R5F10Y44ASP Note

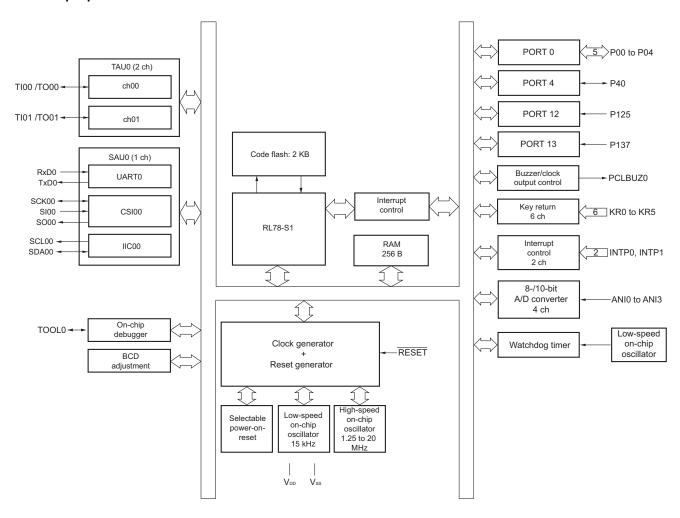
Note Under development

Caution The part number represents the number at the time of publication.

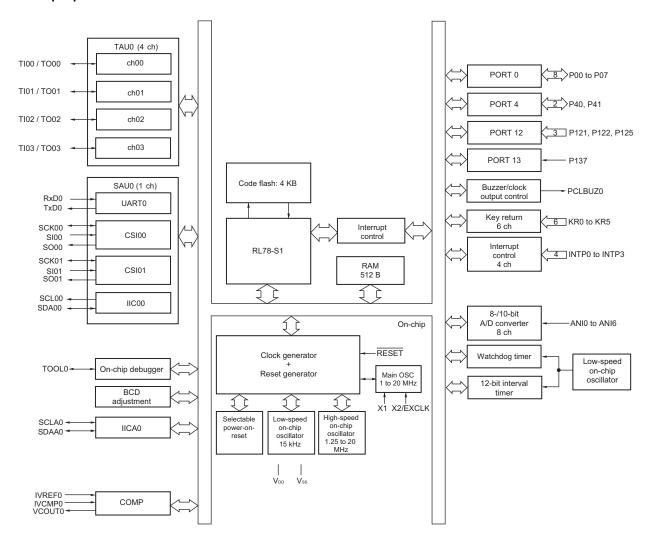
Be sure to review the latest part number through the target product page in the Renesas Electronics Corp.website.

1.5 Block Diagram

1.5.1 10-pin products



1.5.2 16-pin products



1.6 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

Item		10-	-pin	16-pin				
		R5F10Y16ASP	R5F10Y14ASP	R5F10Y47ASP	R5F10Y46ASP	R5F10Y44ASP		
Code flash m	emory	2 KB	1 KB	4 KB	2 KB	1 KB		
RAM		256 B	128 B	512 B	256 B	128 B		
	High-speed system clock	_		, ,				
	High-speed on-chip	• 1.25 to 20 MHz (VDD	= 2.7 to 5.5 V)	1				
	oscillator clock	• 1.25 to 5 MHz (VDD =	= 2.0 to 5.5 V)					
Low-speed or clock	n-chip oscillator	15 kHz (TYP)	,					
General-purp	ose register	8-bit register × 8						
Minimum inst time	truction execution	0.05 μs (20 MHz opera	tion)					
Instruction se	et	Data transfer (8 bits)						
		Adder and subtractor	r/logical operation (8 bits)				
		Multiplication (8 bits:	× 8 bits)					
		Rotate, barrel shift, a (set, reset, test, and I	and bit manipulation Boolean operation), etc.					
I/O port	Total	8 14						
	CMOS I/O	6 (N-ch open-drain out	out (VDD tolerance): 2)	10 (N-ch open-drain output (VDD tolerance): 4)				
	CMOS input	2		4				
Timer	16-bit timer	2 channels		4 channels				
	Watchdog timer	1 channel		Ţ				
	12-bit interval timer	_		1 channel				
	Timer output	2 channels (PWM outp	ut: 1)	4 channels (PW	/M outputs: 3 ^{Note 1})			
Clock output/	buzzer output	1						
		2.44 kHz to 10 MHz: (P	eripheral hardware clock		operation)			
Comparator		_		1				
8-/10-bit reso	olution A/D converter	4 channels		8 channels				
Serial interfac	ce		1 channel/simplified I^2C : 2 channels/simplified I^2C :					
	I ² C bus	_		1 channel				
Vectored	Internal	8		14				
interrupt sources	External	3		5				
Key interrupt		6						
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by selectable power-on-reset Internal reset by illegal instruction execution Note 2 Internal reset by data retention lower limit voltage 						
Selectable po	ower-on-reset circuit	Detection voltage: 2.0 \	//2.4 V/2.7 V/4.0 V					
On-chip debu	ug function	Provided						
Power supply	voltage	V _{DD} = 2.0 to 5.5 V						
Operating arr	nbient temperature	Ta = - 40 to + 85 °C						

Notes 1. The number of outputs varies, depending on the setting of channels in use and the number of the master (see 6.8.3 Operation as multiple PWM output function in the RL78/G10 User's Manual).

2. The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not issued by emulation with the on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

- Cautions 1. This chapter explains the electrical specifications of two products, the R5F10Y16ASP and the R5F10Y14ASP.
 - 2. Electrical specifications for the 16-pin products are T. B. D. because these products are under development.
 - 3. The RL78/G10 has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 4. The pins mounted depend on the product. Refer to 2.1 Port Functions and 2.2.1 Functions for each product in the RL78/G10 User's Manual.

2.1 Absolute Maximum Ratings

$(T_A = 25^{\circ}C)$

Parameter	Symbols	Co	onditions	Ratings	Unit
Supply Voltage	V _{DD}			-0.5 to +6.5	V
Input Voltage	VII			-0.3 to V _{DD} + 0.3 ^{Note}	V
Output Voltage	V _{O1}			-0.3 to V _{DD} + 0.3	V
Output current, high	І он1	Per pin		-40	mA
		Total of all pins	P40	-40	mA
		-140 mA	P00 to P04	-100	mA
Output current, low	I _{OL1}	Per pin	·	40	mA
		Total of all pins	P40	40	mA
		140 mA	P00 to P04	100	mA
Operating ambient temperature	TA			-40 to +85	°C
Storage temperature	T _{stg}			-65 to +150	°C

Note Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. The reference voltage is Vss.

2.2 Oscillator Characteristics

2.2.1 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator oscillation clock frequency Notes 1, 2	fін		1.25		20	MHz
High-speed on-chip oscillator oscillation		Ta = -20 to +85°C	-2.0		+2.0	%
clock frequency accuracy		Ta = -40 to -20°C	-3.0		+3.0	%
Low-speed on-chip oscillator oscillation clock frequency Note 3	fı∟			15		kHz
Low-speed on-chip oscillator oscillation clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 2 of option byte (000C2H).

- 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.
- 3. This only indicates the oscillator characteristics.



2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	P00, P01, P02 to P04, P40	Per pin				-10.0 ^{Note 2}	mA
high ^{Note 1}		P40	Total ^{Note 3}	$4.0~V \leq V_{DD} \leq 5.5~V$			-10.0	mA
				$2.7~V \leq V_{DD} < 4.0~V$			-2.0	mA
				$2.0 \text{ V} \le V_{DD} < 2.7 \text{ V}$			-1.5	mA
		P00, P01, P02 to P04	Total ^{Note 3}	$4.0~V \leq V_{DD} \leq 5.5~V$			-50.0	mA
				$2.7~V \leq V_{DD} < 4.0~V$			-10.0	mA
				$2.0~V \leq V_{DD} < 2.7~V$			-7.5	mA
		Total of all pins ^{Note 3}					-60.0	mA
Output current,	l _{OL1}	P00 to P04, P40	Per pin				20.0 ^{Note 2}	mA
Iow ^{Note 4}		P40	Total ^{Note 3}	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
				$2.7~V \leq V_{DD} < 4.0~V$			3.0	mA
				$2.0~V \leq V_{DD} < 2.7~V$			0.6	mA
		P00 to P04	Total ^{Note 3}	$4.0~V \le V_{DD} \le 5.5~V$			80.0	mA
				$2.7~V \leq V_{DD} < 4.0~V$			12.0	mA
				$2.0 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$			2.4	mA
		Total of all pins ^{Note 3}					100.0	mA
Input voltage, high	V _{IH1}				0.8 V _{DD}		V _{DD}	V
Input voltage, low	VIL1				0		0.2 V _{DD}	٧
Output voltage, high	V _{OH1}	$4.0~V \leq V_{DD} \leq 5.5~V$		Iон =-10 mA	V _{DD} -1.5			٧
Note 5				Iон =-3.0 mA	V _{DD} -0.7			V
		$2.7~V \leq V_{DD} \leq 5.5~V$		Iон =-2.0 mA	V _{DD} -0.6			٧
		$2.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		Iон =-1.5 mA	V _{DD} -0.5			V
Output voltage, low	V _{OL1}	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$		loL = 20 mA			1.3	V
Note 6				loL = 8.5 mA			0.7	V
		$2.7~V \leq V_{DD} \leq 5.5~V$		loL = 3.0 mA			0.6	V
				loL = 1.5 mA			0.4	V
		$2.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		loL = 0.6 mA			0.4	V
Input leakage current, high	Ішн1	$V_{I} = V_{DD}$					1	μA
Input leakage current,low	ILIL1	VI = VSS					-1	μΑ
On-chip pull-up resistance	R∪	Vı = Vss			10	20	100	kΩ

- **Notes 1.** Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. Do not exceed the total current value.
 - 3. This is the output current value under conditions where the duty factor ≤ 70%.
 The output current value when the duty factor > 70% can be calculated with the following expression (when changing the duty factor to n%).



- Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80 % and loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

- Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80 % and loL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- **4.** Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- 5. The value under the condition which satisfies the high-level output current (IOH1).
- 6. The value under the condition which satisfies the low-level output current (IoL1).
- Cautions 1. P00 and P01 do not output high level in N-ch open-drain mode.
 - 2. The maximum value of ViH of P00 and P01 is VDD even in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.

2.3.2 Supply current characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		С	onditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	Basic operation	fін = 20 MHz	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		0.91		mA
			Normal	fıн = 20 MHz	V _{DD} = 3.0 V, 5.0 V		1.57	2.04	
			operation	fıн = 5 MHz	V _{DD} = 3.0 V, 5.0 V		0.85	1.15	
	IDD2 Note 2	HALT mode		fн = 20 MHz	$V_{DD} = 3.0 \text{ V}, 5.0 \text{ V}$		350	820	μΑ
				fıн = 5 MHz	V _{DD} = 3.0 V, 5.0 V		290	600	
	IDD3 ^{Note 3}	STOP mode	Э	V _{DD} = 3.0 V			0.56	2.00	μΑ
WDT supply current	lwdт	fı∟ = 15 kHz	fiL = 15 kHz				0.31		μΑ
ADC supply current	IADC	During conv	ersion at the	V _{DD} = 5.0 V			1.30	1.90	mA
Note 5		highest spe	ed	V _{DD} = 3.0 V			0.50		

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the watchdog timer, A/D converter, I/O port, and on-chip pull-up/pull-down resistors.
 - 2. During HALT instruction execution by flash memory.
 - 3. When the high-speed on-chip oscillator is stopped.
 - 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
 - 5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$

(2) CSI mode (master mode, SCKp... internal clock output)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	(MIN.	TYP.	MAX.	Unit	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq V_{DD} \leq 5.5~V$	200			ns
			$2.0~V \leq V_{DD} \leq 5.5~V$	800			ns
SCKp high-/low-level width	tkH1, tkL1	2.7 V ≤ V _{DD} ≤ 5	2.7 V ≤ V _{DD} ≤ 5.5 V				ns
		$2.0~V \leq V_{DD} \leq 5.5~V$		tkcy1/2-50			ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	2.7 V ≤ V _{DD} ≤ 5	5.5 V	47			ns
		2.0 V ≤ V _{DD} ≤ 5	5.5 V	110			ns
SIp hold time (from SCKp↑) Note 2	tksi1						ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note 4				25	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0)

fmcx: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00))

(3) CSI mode (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	fмск = 20 MHz	8/fмск			ns
			fмcк ≤ 10 MHz	6/ƒмск			ns
		$2.0~V \leq V_{DD} < 2.7~V$		6/ƒмск			ns
SCKp high-/low-level width	tĸH2,	$2.0~V \leq V_{DD} \leq 5.5~V$		tkcy2/2			ns
	t _{KL2}						
SIp setup time (to SCKp↑) ^{Note 1}	tsık2	$2.7~\text{V} \le \text{V}_{\text{DD}} \le 5.5~\text{V}$		1/fмcк+ 20			ns
		$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$		1/fмск+ 30			ns
SIp hold time (from SCKp [↑]) Note 2	tksi2	2.0 V ≤ V _{DD} ≤ 5.5 V		1/fмск+ 31			ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note 4	2.7 V ≤ V _{DD} ≤ 5.5 V			2/fмcк+50	ns
			$2.0 \text{ V} \leq \text{V}_{\text{DD}} < 2.7$ V			2/fмск+ 110	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(4) Simplified I²C mode

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$2.0~V \leq V_{DD} \leq 5.5~V,$		400 Note 1	kHz
		$C_b=100~pF,~R_b=3~k\Omega$			
Hold time when SCLr = "L"	tLOW	$2.0~V \leq V_{DD} \leq 5.5~V,$	1150		ns
		$C_b=100~pF,~R_b=3~k\Omega$			
Hold time when SCLr = "H"	tніgн	$2.0~V \leq V_{DD} \leq 5.5~V,$	1150		ns
		$C_b=100~pF,~R_b=3~k\Omega$			
Data setup time (reception)	tsu: dat	$2.0~V \leq V_{DD} \leq 5.5~V,$	1/fмск +		ns
		$C_b=100~pF,~R_b=3~k\Omega$	145 Note 2		
Data hold time (transmission)	thd: dat	$2.0~V \leq V_{DD} \leq 5.5~V,$	0	355	ns
		$C_b=100~pF,~R_b=3~k\Omega$			

- Notes 1. The value must also be equal to or less than fmck/4.
 - 2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

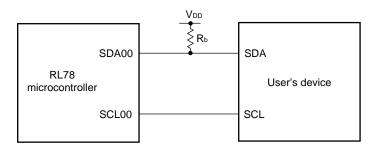
Caution Select the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin by using the port output mode register 0 (POM0).

Remarks 1. R_b [Ω]: Communication line (SDAr) pull-up resistance, C_b [F]: Communication line (SCLr, SDAr) load capacitance

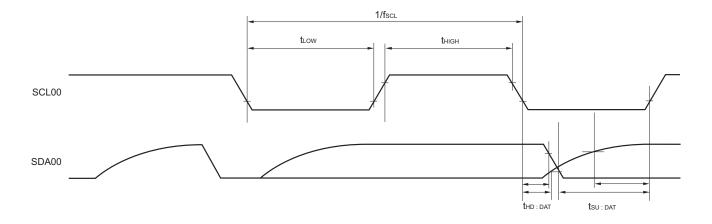
- **2.** r: IIC number (r = 00)
- 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00))



Simplified I²C mode connection diagram



Simplified I²C mode serial transfer timing



2.6.4 Data retention power supply voltage characteristics

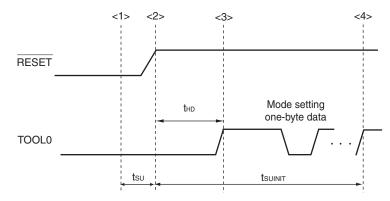
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention power supply voltage	VDDDR		1.9		5.5	V
range						

Caution Data is retained until the power supply voltage becomes under the minimum value of the data retention power supply voltage range. Note that data in the RAM and RESF registers might not be cleared even if the power supply voltage becomes under the minimum value of the data retention power supply voltage range.

2.9 Timing of Entry to Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	SPOR reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	SPOR reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends	thD	SPOR reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (SPOR reset must end before the external reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of entry to the flash memory programming mode by UART reception.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends (MIN. 10 μ s)

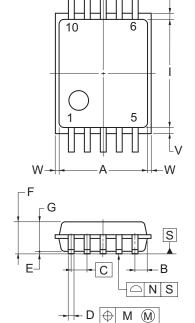
thd: How long to keep the TOOL0 pin at the low level from when the external reset ends

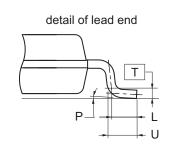
3. PACKAGE DRAWINGS

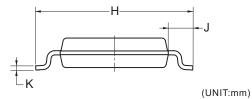
3.1 10-pin products

R5F10Y16ASP, R5F10Y14ASP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP10-4.4x3.6-0.65	PLSP0010JA-A	P10MA-65-CAC-2	0.05







ITEM DIMENSIONS Α 3.60 ± 0.10 В 0.50 С 0.65 (T.P.) D 0.24±0.08 Ε 0.10 ± 0.05

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

F	F 1.45 MAX.	
G	1.20 ± 0.10	
Н	6.40±0.20	
I	4.40 ± 0.10	
J	1.00±0.20	
K	$0.17^{+0.08}_{-0.07}$	
L	0.50	
М	0.13	
N	0.10	
Р	3° +5° -3°	
Т	0.25 (T.P.)	
U	0.60 ± 0.15	
V	0.25 MAX.	
W	0.15 MAX.	

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Revision History	RL78/G10 Data Sheet
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		Description		
Rev.	Date	Page	Summary	
1.00	Apr 15, 2013	-	First Edition issued	

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.